



SHEET OF

Form PTO 1449
(Modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.
242330US2S

SERIAL NO.
10/653,976

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT
Kentaro NAKAJIMA

FILING DATE
September 4, 2003

GROUP
2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Uet	AA	6,473,336	10/29/02	NAKAJIMA et al.	—	—	—
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AQ					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW		
	AX		
	AY		
	AZ		

☐ Additional References sheet(s) attached

Examiner LONG TRIM

Date Considered 11/5/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 242330US2S		SERIAL NO. 10/653,976	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Kentaro NAKAJIMA		GROUP	
				FILING DATE September 4, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Uet	AA	6,429,044	08/06/2002	M. TUTTLE	—	—	—
Uet	AB	5,939,772	08/17/1999	A. T. HURST, et al.	—	—	—
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
Uet	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, ISSCC 2000 / Session 7/ TD: Emerging Memory & Device Technologies / Paper 7.2, pages 128-129, "TA 7.2 A 10ns READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000					
Uet	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997					
Uet	AY	M. SATO, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 28, pages L200-L201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997					
Uet	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 108, pages L 1380-L 1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner LONG TRAM					Date Considered 4/5/05		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							